Exceptionally Low Forward Voltage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench–based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These are Pb–Free and Halide–Free Devices

Typical Applications

- Switching Power Supplies including Wireless, Smartphone and Notebook Adapters
- High Frequency and DC–DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics:

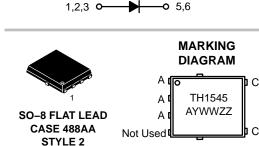
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting SurfaceTemperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



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SCHOTTKY BARRIER RECTIFIERS 15 AMPERES 45 VOLTS



TH1545 = Specific Device Code

A = Assembly Location

- A33

γ

- = Year
- W = Work Week
- ZZ = Lot Traceability

Device	Package	Shipping†		
NTS1545MFST1G	SO–8 FL (Pb–Free)	1500 / Tape & Reel		
NTS1545MFST3G	SO–8 FL (Pb–Free)	5000 / Tape & Reel		
NRVTS1545MFST1G	SO–8 FL (Pb–Free)	1500 / Tape & Reel		
NRVTS1545MFST3G	SO–8 FL (Pb–Free)	5000 / Tape & Reel		

ORDERING INFORMATION

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V	
Average Rectified Forward Current (Rated V_R , T_C = 142°C)	I _{F(AV)}	15	A	
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, T_C = 140°C)	I _{FRM}	30	A	
Non–Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	210	A	
Storage Temperature Range	T _{stg}	-65 to +150	°C	
Operating Junction Temperature	TJ	-55 to +150	°C	
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E _{AS}	100	mJ	
ESD Rating (Human Body Model)		3B		
ESD Rating (Machine Model)		M4		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{ extsf{ heta}JC}$	1.3	-	°C/W

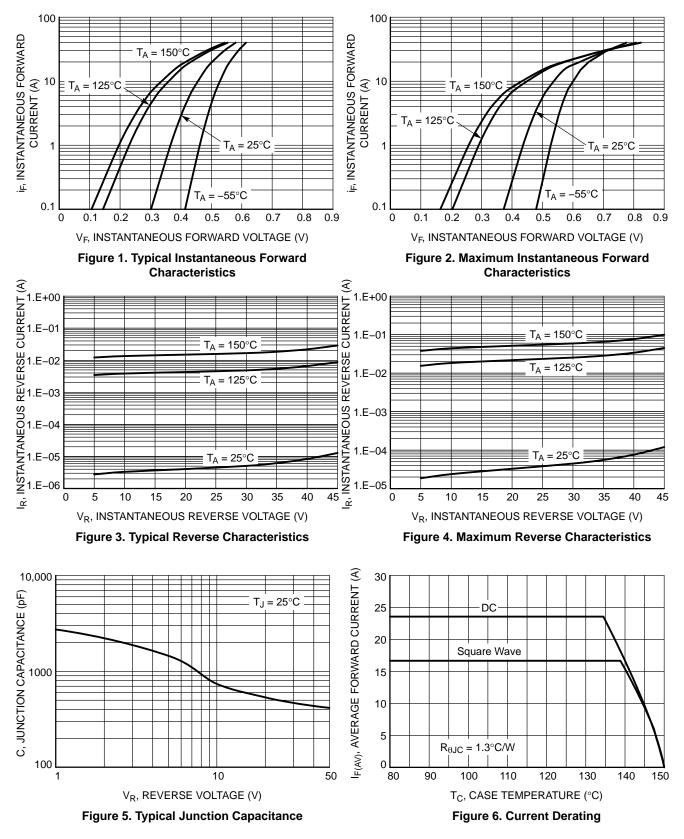
ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1)	VF			V
$(i_{\rm F} = 5.0 \text{ Amps}, T_{\rm J} = 25^{\circ} \text{C})$		0.42	_	
(i _F = 7.5 Amps, T _J = 25°C)		0.45	-	
$(i_F = 15 \text{ Amps}, T_J = 25^{\circ}\text{C})$		0.48	0.57	
(i _F = 5.0 Amps, T _J = 125°C)		0.31	-	
(i _F = 7.5 Amps, T _J = 125°C)		0.34	-	
(i _F = 15 Amps, T _J = 125°C)		0.40	0.51	
Instantaneous Reverse Current (Note 1)	i _R			
(Rated dc Voltage, $T_J = 25^{\circ}C$)		-	120	μΑ
(Rated dc Voltage, $T_J = 125^{\circ}C$)		15	45	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

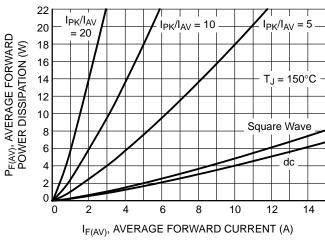


Figure 7. Forward Power Dissipation

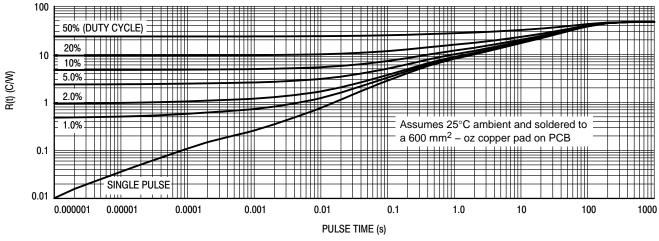
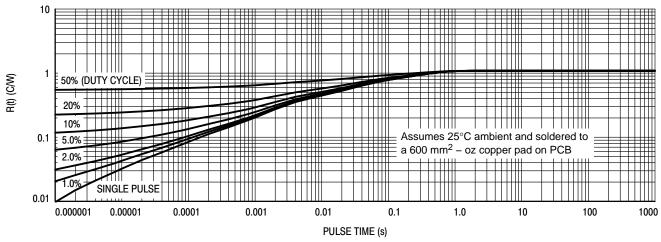
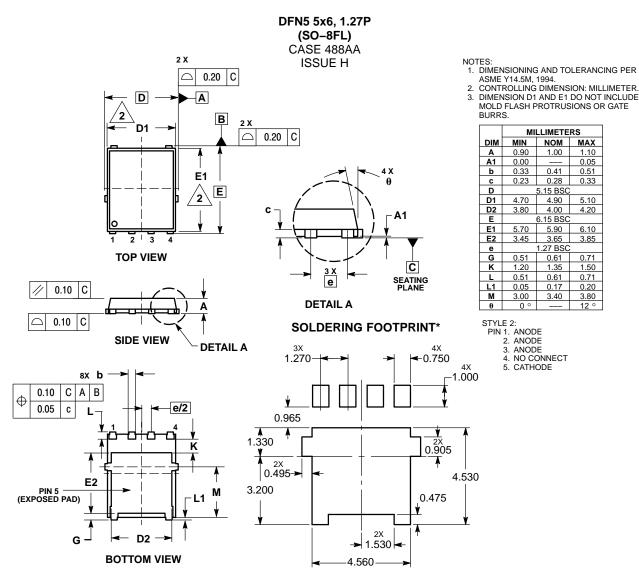


Figure 8. Typical Thermal Characteristics





PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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